

Photocouplers Infrared LED & Photo Transistor

TLP291(SE

1. Applications

- · Switching Power Supplies
- · Programmable Logic Controllers (PLCs)
- · I/O Interface Boards

2. General

TLP291(SE consists of photo transistor optically coupled to an infrared emitting diode. TLP291(SE is housed in the SO4 package, very small and thin coupler. Since TLP291(SE is guaranteed wide operating temperature (T_a = -55 to 110 °C) and high isolation voltage (3750 Vrms), it's suitable for high-density surface mounting applications such as small switching power supplies and programmable controllers.

3. Features

- (1) Collector-emitter voltage: 80 V (min)
- (2) Current transfer ratio: 50 % (min)

GB Rank: 100 % (min)

- (3) Isolation voltage: 3750 Vrms (min)
- (4) Operating temperature: -55 to 110 °C
- (5) Safety standards

UL-recognized: UL 1577, File No.E67349

cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349

VDE-approved: EN 60747-5-5, EN 62368-1 (Note 1)

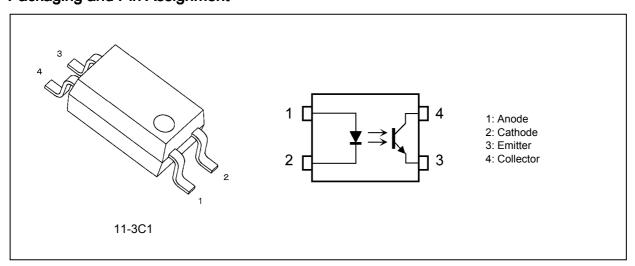
CQC-approved: GB4943.1, GB8898 Japan and Thailand Factory



仅适用干海拔 2000m 以下地区安全使用

Note 1: When a VDE approved type is needed, please designate the Option (V4).

4. Packaging and Pin Assignment



Start of commercial production

2012-02



5. Mechanical Parameters

Characteristics	Min	Unit
Creepage distances	5.0	mm
Clearance	5.0	
Internal isolation thickness	0.4	

6. Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25 °C)

	Characteristics	3	Symbol	Note	Rating	Unit
LED	Input forward current		I _F		50	mA
	Input forward current derating	(T _a ≥ 90 °C)	$\Delta I_F/\Delta T_a$		-1.5	mA/°C
	Input forward current (pulsed)		I _{FP}	(Note 1)	1	Α
	Input reverse voltage		V_R		5	V
	Input power dissipation		P_{D}		100	mW
	Input power dissipation derating	(T _a ≥ 90 °C)	$\Delta P_D/\Delta T_a$		-3.0	mW/°C
	Junction temperature		Tj		125	°C
Detector	Collector-emitter voltage		V _{CEO}		80	V
	Emitter-collector voltage		V _{ECO}		7	V
	Collector current		I _C		50	mA
	Collector power dissipation		Pc		150	mW
	Collector power dissipation derating	$(T_a \ge 25 \text{ °C})$	$\Delta P_{C}/\Delta T_{a}$		-1.5	mW/°C
	Junction temperature		Tj		125	°C
Common	Operating temperature		T _{opr}		-55 to 110	°C
	Storage temperature		T _{stg}		-55 to 125	°C
	Lead soldering temperature	(10 s)	T _{sol}		260	°C
	Total power dissipation		P _T		200	mW
	Total power dissipation derating	(T _a ≥ 25 °C)	$\Delta P_T / \Delta T_a$		-2.0	mW/°C
	Isolation voltage	AC, 60 s, R.H. ≤ 60 %	BV _S	(Note 2)	3750	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width (PW) \leq 0.1 ms, f = 100 Hz

Note 2: This device is considered as a two-terminal device: Pins 1 and 2 are shorted together, and pins 3 and 4 are shorted together.

7. Electrical Characteristics (Unless otherwise specified, T_a = 25 °C)

	Characteristics	Symbol	Note	Test Condition	Min	Тур.	Max	Unit
LED	Input forward voltage	V _F		I _F = 10 mA	1.1	1.25	1.4	V
	Input reverse current	I _R		V _R = 5 V			5	μΑ
	Input capacitance	Ct		V = 0 V, f = 1 MHz	_	30		pF
Detector	Collector-emitter breakdown voltage	V _{(BR)CEO}		I _C = 0.5 mA	80			V
	Emitter-collector breakdown voltage	V _{(BR)ECO}		I _E = 0.1 mA	7			V
	Dark Current	I _{DARK}		V _{CE} = 48 V		0.001	0.08	μΑ
				V _{CE} = 48 V, T _a = 85 °C	_	2	50	
	Collector-emitter capacitance	C _{CE}		V = 0 V, f = 1 MHz	_	10	_	pF



8. Coupled Electrical Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Тур.	Max	Unit
Current transfer ratio	I _C /I _F	(Note 1)	I _F = 5 mA, V _{CE} = 5 V	50	-	600	%
			I_F = 5 mA, V_{CE} = 5 V, Rank GB	100		600	
Saturated current transfer ratio	I _C /I _{F(sat)}		I _F = 1 mA, V _{CE} = 0.4 V	_	60		
			I_F = 1 mA, V_{CE} = 0.4 V, Rank GB	30			
Collector-emitter saturation voltage	V _{CE(sat)}		I _C = 2.4 mA, I _F = 8 mA	_		0.3	٧
			I _C = 0.2 mA, I _F = 1 mA	_	0.12	_	
	V _{CE(sat)}		I _C = 0.2 mA, I _F = 1 mA, Rank GB	_	_	0.3	
OFF-state collector current	I _{C(off)}		V _F = 0.7 V, V _{CE} = 48 V	_		10	μΑ

Note 1: See Table 8.1 for current transfer ratio.

Table 8.1 Current Transfer Ratio (CTR) Rank (Note) (Unless otherwise specified, Ta = 25 °C)

Rank	Rank short code	Note	Test Condition	Current transfer ratio I _C /I _F (min)	Current transfer ratio I _C /I _F (max)	Marking of classification	Unit
Blank	I		$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	50	600	Blank, YE, GR, GB, BL, Y+, G, G+, B	%
Υ			$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	50	150	YE, Y+	
GR			$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	100	300	GR, G, G+	
GB			$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	100	600	GB, GR, G, G+, BL, B	
BL			$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	200	600	BL, B	
YH	ı		$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	75	150	Y+	
GRL	GL	(Note 1)	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	100	200	G	
GRH	GH	(Note 1)	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	150	300	G+	
BLL	В	(Note 1)	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	200	400	В	

Note: Specify both the part number and a rank in this format when ordering.

Example: TLP291(GB,SE

For safety standard certification, however, specify the part number alone.

Example: TLP291(GB,SE → TLP291

Note 1: A rank in the order name is sometimes omitted like above "Rank short code".

9. Isolation Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Тур.	Max	Unit
Total capacitance (input to output)	Cs	(Note 1)	V _S = 0 V, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R _S	(Note 1)	V _S = 500 V, R.H. ≤ 60 %	1 × 10 ¹²	1014		Ω
Isolation voltage	BVS	(Note 1)	AC, 60 s	3750			Vrms

Note 1: This device is considered as a two-terminal device: Pins 1 and 2 are shorted together, and pins 3 and 4 are shorted together.



10. Switching Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Тур.	Max	Unit
Rise time	t _r		V _{CC} = 10 V, I _C = 2 mA,	_	2	_	μS
Fall time	t _f		$R_L = 100 \Omega$	_	3	_	
Turn-on time	t _{on}			_	3	_	
Turn-off time	t _{off}			_	3	_	
Turn-on time	t _{on}		See Fig. 10.1	_	0.5	_	
Storage time	ts		$R_L = 1.9 \text{ k}\Omega, V_{CC} = 5 \text{ V},$ $I_F = 16 \text{ mA}$	_	25	_	
Turn-off time	t _{off}		ווי – וט ווויא	_	40		

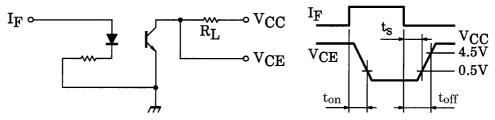


Fig. 10.1 Switching Time Test Circuit and Waveform



11. Characteristics Curves (Note)

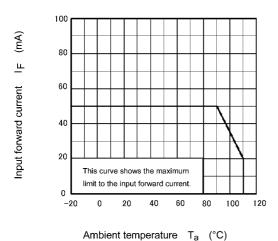


Fig. 11.1 I_F - T_a

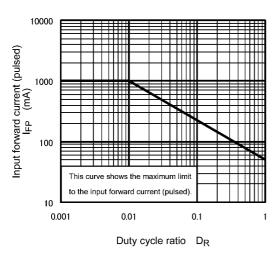


Fig. 11.3 I_{FP} - D_R

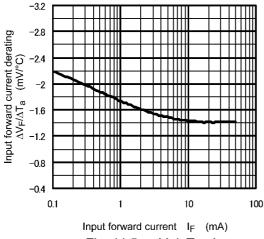
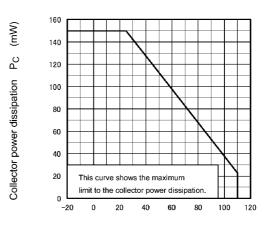


Fig. 11.5 $\Delta V_F/\Delta T_a - I_F$



Ambient temperature T_a (°C)

Fig. 11.2 P_C - T_a

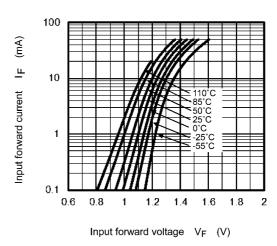


Fig. 11.4 IF - VF

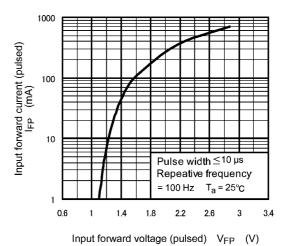


Fig. 11.6 I_{FP} - V_{FP}



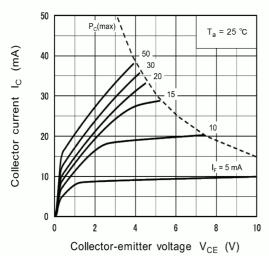


Fig. 11.7 I_C - V_{CEO}

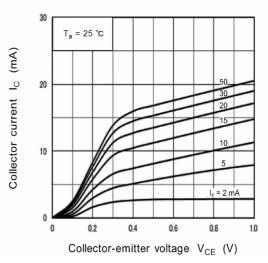


Fig. 11.8 I_C - V_{CEO}

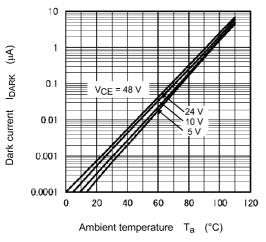


Fig. 11.9 I_{DARK} - T_a

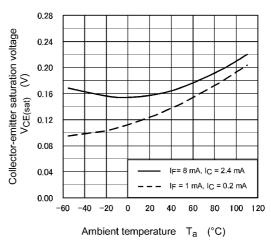


Fig. 11.10 V_{CE(sat)} - T_a

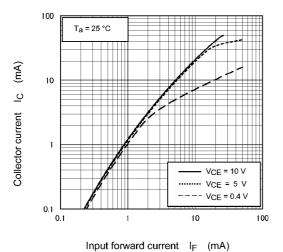


Fig. 11.11 I_C - I_F

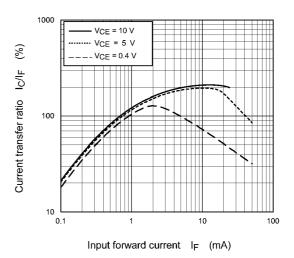
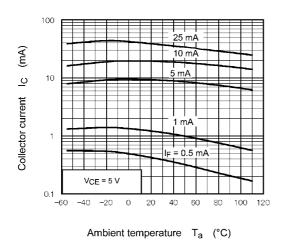


Fig. 11.12 I_C/I_F - I_F





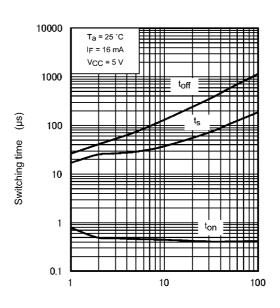
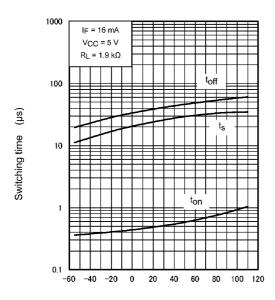


Fig. 11.13 I_C - T_a

Fig. 11.14 Switching Time - RL

Load resistance R_L (k Ω)



 $\label{eq:ambient temperature} \begin{array}{ll} \text{Ambient temperature} & T_a \quad (^\circ\text{C}) \\ \\ \textbf{Fig. 11.15} & \textbf{Switching Time - T}_a \\ \end{array}$

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



12. Soldering and Storage

12.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

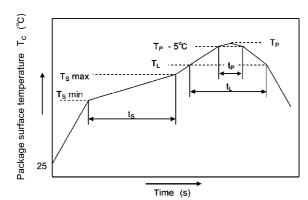
· When using soldering reflow.

The soldering temperature profile is based on the package surface temperature.

(See the figure shown below, which is based on the package surface temperature.)

Reflow soldering must be performed once or twice.

The mounting should be completed with the interval from the first to the last mountings being 2 weeks.



	Symbol	Min	Max	Unit
Preheat temperature	Ts	150	200	°C
Preheat time	ts	60	120	S
Ramp-up rate (T _L to T _P)			3	°C/s
Liquidus temperature	TL	217		°C
Time above T _L	t∟	60	150	s
Peak temperature	T _P		260	°C
Time during which T_c is between $(T_P - 5)$ and T_P	t _P		30	s
Ramp-down rate (T _P to T _L)			6	°C/s

Fig. 12.1.1 An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

· When using soldering flow

Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds. Mounting condition of 260 °C within 10 seconds is recommended.

Flow soldering must be performed once.

· When using soldering Iron

Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C

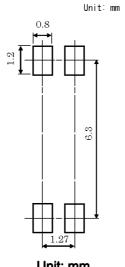
Heating by soldering iron must be done only once per lead.

12.2. Precautions for General Storage

- · Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- · When restoring devices after removal from their packing, use anti-static containers.
- · Do not allow loads to be applied directly to devices while they are in storage.
- If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.

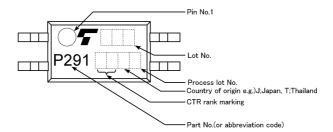


13. Land Pattern Dimensions (for reference only)



Unit: mm

14. Marking



Rev.2.0



15. EN 60747-5-5 Option (V4) Specification

· Part number: TLP291 (Note 1)

• The following part naming conventions are used for the devices that have been qualified according to option (V4) of EN 60747.

Example: TLP291(V4GBTL,SE

V4: EN 60747 option

GB: CTR rank

TL: Tape type (L direction:TPL)
E: [[G]]/RoHS COMPATIBLE (Note 2)

Note 1: Use TOSHIBA standard type number for safety standard application.

e.g., TLP291(V4GBTL,SE → TLP291

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Description	Symbol	Rating	Unit
Application classification			
for rated mains voltage \leq 150 Vrms for rated mains voltage \leq 300 Vrms		I-IV I-III	_
Climatic classification		55 / 125 / 21	_
Pollution degree		2	_
Maximum operating insulation voltage	VIORM	707	Vpeak
Input to output test voltage, Method A $V_{pr} = 1.6 \times \text{VIORM, type and sample test} \\ t_p = 10 \text{ s, partial discharge} < 5 \text{ pC}$	Vpr	1131	Vpeak
Input to output test voltage, Method B Vpr =1.875 × VIORM, 100 % production test tp = 1 s, partial discharge < 5 pC	Vpr	1330	Vpeak
Highest permissible overvoltage (transient overvoltage, tpr = 60 s)	VTR	6000	Vpeak
Safety limiting values (max. permissible ratings in case of fault, also refer to thermal derating curve) current (input current IF, Pso = 0) power (output or total power dissipation) temperature	Isi Pso Ts	250 400 150	mA mW °C
Insulation resistance $VIO = 500 \text{ V}, T_a = 25 \text{ °C}$ $VIO = 500 \text{ V}, T_a = 100 \text{ °C}$ $VIO = 500 \text{ V}, T_a = T_s$	Rsi	≥ 10 ¹² ≥ 10 ¹¹ ≥ 10 ⁹	Ω

Fig. 15.1 EN 60747 Insulation Characteristics



Table Insulation Related Specifications (Note)

Insulation Related Parameters	Symbol	TLP291
Minimum creepage distance	Cr	5.0 mm
Minimum clearance	CI	5.0 mm
Minimum insulation thickness	ti	0.4 mm
Comparative tracking index	CTI	175

Note: This photocoupler is suitable for **safe electrical isolation** only within the safety limit data. Maintenance of the safety data shall be ensured by means of protective circuits.



Fig. 15.2 Marking on packing for EN 60747

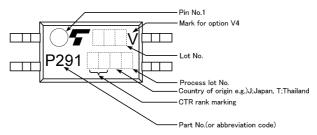
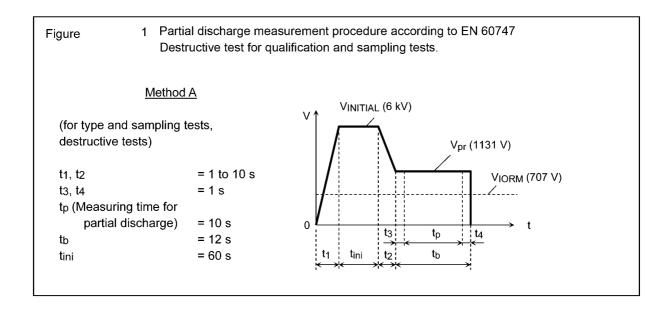


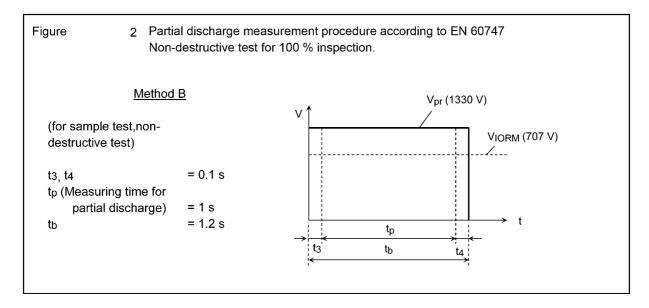
Fig. 15.3 Marking Example (Note)

Note: The above marking is applied to the photocouplers that have been qualified according to option (V4) of EN 60747.

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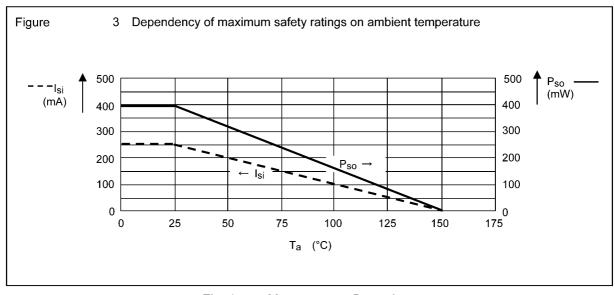


Fig. 15.4 Measurement Procedure

Rev.2.0



15.1. Ordering Information

When placing an order, please specify the part number, CTR rank, tape type and quantity as shown in the following example.

Example) TLP291(GB-TP,SE 5000 pcs

Part number: TLP291

CTR rank: GB

Tape type: TP (L direction)

[[G]]/RoHS COMPATIBLE: E (Note 1)

Quantity (must be a multiple of 2500): 5000 pcs

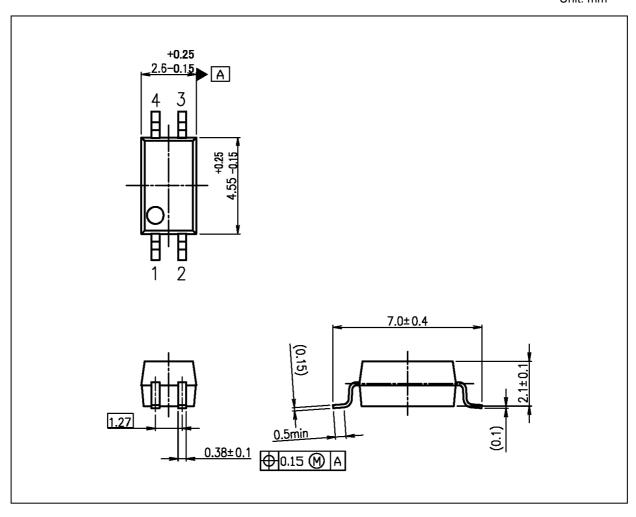
Note 1: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



Package Dimensions

Unit: mm



Weight: 0.05 g (typ.)

	Package Name(s)
TOSHIBA: 11-3C1	



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